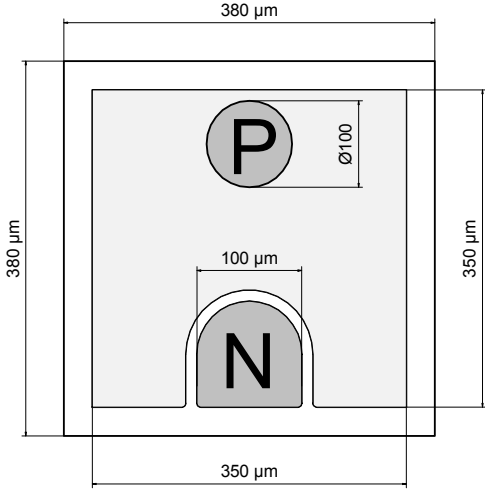


Radiation	Type	Technology	Electrodes
Violet	Standard	InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions in µm (±20 µm)	
	<u>typ. thickness</u> 90 (±20) µm <u>cathode</u> gold alloy, 1.5 µm <u>anode</u> gold alloy, 1.5 µm	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		3,6	4,5	V
Reverse voltage	I _F = 10 µA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	1,9	3,0		mW
Radiant intensity ¹	I _F = 20 mA	I _e	1,0	1,3		mW/sr
Peak wavelength	I _F = 20 mA	λ _p	400	410	420	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		17		nm
Switching time	I _F = 20 mA	t _r , t _f		20		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-410-37				

Packing: Chips on adhesive film with wire-bond side on top